

MILITARY SPECIFICATION

SEMICONDUCTOR DEVICE, TRIODE THYRISTOR (BI-DIRECTIONAL), SILICON.

TYPES 2N5806 THROUGH 2N5809

This amendment forms a part of Military Specification MIL-S-19500/438, dated 20 August 1970, and is approved for use by all Departments and Agencies of the Department of Defense.

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Table III, group C inspection, subgroup 7, delete and substitute:

Examination or test	MIL-STD-750		LTPD	Symbol	Limits		Unit
	Method	Details			Min	Max	
<u>Subgroup 7</u>			$\lambda=20$				
Off-state voltage life test	---	(See figure 3) $T_C = 115^\circ\text{C}$		---			
2N5806		$V_{\text{DRM}} = 200 \text{ v(pk)}$			---	---	---
2N5807		$V_{\text{DRM}} = 400 \text{ v(pk)}$			---	---	---
2N5808		$V_{\text{DRM}} = 500 \text{ v(pk)}$			---	---	---
2N5809		$V_{\text{DRM}} = 600 \text{ v(pk)}$			---	---	---
End points: (See 4.5.3.)							
Thermal fatigue		$I_{\text{T(RMS)}} = 25\text{A}, 60\text{Hz}$ $\Delta T = 40^\circ\text{C}$ (1 Min. on, 3 Min. off ± 5 Min = 1 cycle) 4,000 cycles					
End points: (see 4.5.3) Same as subgroup 4 of group B.							

Custodians:

Army - EL
Navy - EC
Air Force - 17

Review activities:

Army - MJ, MI
Navy -
Air Force - 11, 19, 80, 85
DSA - ES
NASA - NA

User activities:

Army - SM
Navy - CG, MC, OS, AS, SH

Preparing activity:
Navy - EC

Agent:
DSA - ES

(Project 5961-0613)